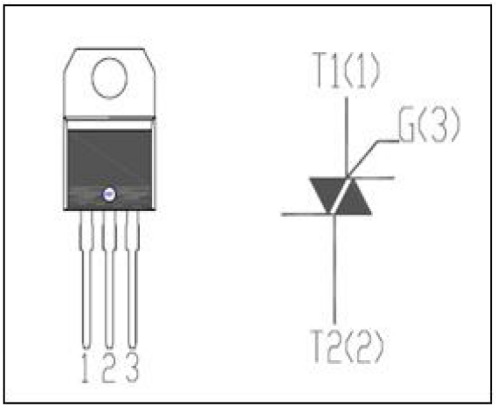
BTA26-800B

DESCRIPTION

- With TO-3PN packaging
- Operating in 4 quadrants
- High voltage capability;high current capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Applications subject to high temperature
- Heating controls; high power motor control
- High power switching

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		MAX	UNIT
V_{DRM}	Repetitive peak off-state voltage		800	V
V_{RRM}	Repetitive peak reverse voltage		800	V
$I_{T(RSM)}$	RSM average on-state current Tc=90℃		25	A
I_{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	250 260	A
$P_{G(AV)}$	Average gate power dissipation (over any 20 ms period) @ Tc=125℃		1	W
T_j	Operating junction temperature		-40~125	℃
T_{stg}	Storage temperature		-40~150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_R=V_{RRM} Rated;	Tj=25℃		5	μA
I_{DRM}	Repetitive peak off-state current	V_D=V_{DRM} Rated;	Tj=125℃		3	mA
V_{TM}	On-state voltage	I_T=35A;t_P=380 μs			1.55	V
I_{GT}	Gate-trigger current	V_D =12V;R_L=33Ω;	I		50	mA
			II		50	
			III		50	
			IV		100	
V_{GT}	Gate-trigger voltage	V_D =12V;R_L=33Ω;			1.3	V
Rth(j-c)	Junction to case				1.1	℃/W